

| | Type | L # | Hits | Search Text | DBs |
|---|------|-----|------|-----------------------------------|--|
| 1 | BRS | L1 | 0 | rekhi near sanjay.in. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 2 | BRS | L2 | 0 | cherukupalli near nagendra.in. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 3 | BRS | L3 | 9 | keswick near paul.in. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 4 | BRS | L4 | 631 | 257/356.ccls. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|---|------|-----|------|--|--|
| 5 | BRS | L5 | 114 | 4 and (first near transistor) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 6 | BRS | L6 | 4 | 4 and (first near transistor) near25 (charge\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 7 | BRS | L7 | 3308 | (first near transistor) near25 (charge\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 8 | BRS | L8 | 0 | (first near transistor) near15 (metal near wire\$1) near25 (charge\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|---|--|
| 9 | BRS | L9 | 5 | (first near transistor) near15 (wire\$1) near25 (charge\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 10 | BRS | L10 | 412 | (transistor) near15 (wire\$1) near25 (charge\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 11 | BRS | L11 | 0 | (transistor) near15 (wire\$1) near25 (charge\$1 near3 buildup) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 12 | BRS | L12 | 0 | (transistor) near15 (wire\$1) near25 (charge\$1 near3 build-up) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|---|--|
| 13 | BRS | L13 | 1 | (transistor) near15 (wire\$1) near25 (build-up) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 14 | BRS | L14 | 3 | (transistor) near15 (wire\$1) near25 (build near up) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 15 | BRS | L15 | 0 | (transistor) near15 (wire\$1) near25 (buildup) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 16 | BRS | L16 | 0 | (second near transistor) near15 (wire\$1) near25 (charge41) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|-------|--|--|
| 17 | BRS | L17 | 4 | (second near transistor) near15 (wire\$1) near25 (charge\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 18 | BRS | L18 | 398 | (second near transistor) near15 (wire\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 19 | BRS | L19 | 11 | (second near transistor) near15 (metal near wire\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 20 | BRS | L20 | 73938 | (transistor) near15 (metal or wire\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|-------|---|--|
| 21 | BRS | L21 | 8 | 20 and (switch\$3 near5 on) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 22 | BRS | L22 | 11 | ((transistor) near15 (metal or wire\$1)) near25 (on) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 23 | BRS | L23 | 11 | ((transistor) near15 (metal or wire\$1)) near15 (on) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 24 | BRS | L24 | 71026 | ((transistor) near15 (charge\$1)) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|--|--|
| 25 | BRS | L25 | 25 | ((transistor) near15 (charge\$1)) near10 (on) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 26 | BRS | L26 | 33 | 24 and (switch\$3 near5 on) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 27 | BRS | L27 | 725 | (switch\$3 near on) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 28 | BRS | L28 | 59 | ((switch\$3 near on)) near15 (transistor) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|-------|---|--|
| 29 | BRS | L29 | 390 | ((on)) near15 (transistor) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 30 | BRS | L30 | 18 | ((on)) near15 (transistor near15 discharg\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 31 | BRS | L31 | 19 | ((on)) near15 (transistor near25 discharg\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 32 | BRS | L32 | 11036 | ((off)) near15 (transistor near25 discharg\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|--|--|
| 33 | BRS | L33 | 330 | ((off)) near15 (second near transistor) near25 (discharg\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 34 | BRS | L34 | 4 | ((off)) near15 (second near transistor) near25 (metal or wire\$1) near25 (discharg\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 35 | BRS | L35 | 21 | (second near transistor) near25 (metal or wire\$1) near25 (discharg\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 36 | BRS | L36 | 238 | ((transistor) near25 (metal or wire\$1) near25 (discharg\$3)) near15 (protect\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|---|--|
| 37 | BRS | L37 | 14 | ((transistor) near25 (metal or wire\$1) near25 (discharg\$3)) near15 (protect\$3 near5 gate) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 38 | BRS | L38 | 61 | 36 and charge | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 39 | BRS | L39 | 69 | 36 and (coupl\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 40 | BRS | L40 | 12 | ((coupl\$3 near15 transistor) near25 (metal or wire\$1) near25 (discharg\$3)) near15 (protect\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|-------|---|--|
| 41 | BRS | L41 | 20513 | (transistor near15 float\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 42 | BRS | L42 | 1080 | (transistor near15 float\$3) near15 (metal\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 43 | BRS | L43 | 9 | (discharg\$3) near10 (transistor near15 float\$3) near15 (metal\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 44 | BRS | L44 | 425 | (discharg\$3) near10 (transistor) near15 (metal\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|---|--|
| 45 | BRS | L45 | 127 | (discharg\$3) near10 (transistor) near15 (protect\$3 near10 metal\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | U | 1 | Document ID | Title |
|---|---|---|---------------|---|
| 1 | | | US 6545915 B2 | Method for driving nonvolatile semiconductor memory device |
| 2 | | | US 5528547 A | Electrically erasable programmable read-only memory with electric field decreasing controller |
| 3 | | | US 5402373 A | Electrically erasable programmable read-only memory with electric field decreasing controller |
| 4 | | | US 5293337 A | Electrically erasable programmable read-only memory with electric field decreasing controller |
| 5 | | | US 4665503 A | Non-volatile memory devices |
| 6 | | | US 4375087 A | Electrically erasable programmable read only memory |
| 7 | | | JP 08250609 A | SEMICONDUCTOR STORAGE DEVICE AND USAGE THEREOF |

| | U | 1 | Document ID | Title |
|---|---|---|---------------------|--|
| 8 | X | | US 20030007389 A | Nonvolatile semiconductor memory device drive method e.g. for rewritable flash memory, involves setting MOS transistor between local and main bit lines to half-conducting state and applying preset voltage to control gate |
| 9 | X | | EP 1158535 A | Semiconductor memory device for computer system, detects memory cells which are over erased by collective erasing and writes data to over erased memory cells |